



PATENT APPLICATION

AF/2813
RCE/2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Teruo Takizawa et al.

Group Art Unit: 2813

Application No.: 09/763,365

Examiner: D. Hogans

Filed: February 23, 2001

Docket No.: 108680

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

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**LARGE ENTITY REQUEST FOR
CONTINUED EXAMINATION UNDER 37 C.F.R. §1.114**

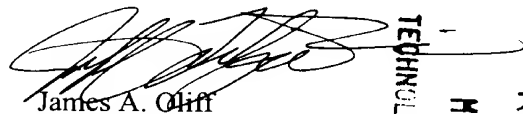
Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. §1.114, Applicants hereby request continued examination, entry and consideration of the attached Amendment. The above-identified application was filed on or after June 8, 1995. Thus, entry is proper under 37 C.F.R. §1.114(d).

Attached hereto is our check no. 139417 in the amount of ☒ \$750.00 as payment of the fees set forth in 37 C.F.R. §1.17(e). The Director is hereby authorized to charge any additional fees or credit any overpayment associated with this communication to Deposit Account No. 15-0461. Two duplicate copies of this page are enclosed.

Respectfully submitted,


James A. Oliff

Registration No. 27,075

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JAO:JML/vgp

Attachments:

Amendment Under 37 C.F.R. §1.114

Date: February 26, 2003

OLIFF & BERRIDGE, PLC
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PATENT APPLICATION

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For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

AMENDMENT UNDER 37 C.F.R. §1.114

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

Prior to initial Examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 1-16 without prejudice to or disclaimer of the subject matter contained therein.

Please add new claims 17-27 as follows:

--17. A semiconductor device, comprising:

a metal-oxide-semiconductor field-effect transistor including:

a silicon substrate,

a gate insulation film on the silicon substrate, and

a gate electrode on the gate insulation film, the gate electrode including

a germanium film on the gate insulation film,

wherein p-type impurities are doped into the germanium film, and a range of concentration of the p-type impurities is about 10^{17} to 10^{20} cm^{-3} .--

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